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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/661,793	09/12/2003	Chi-An Kao	TS01-1037	8353
8933 DHANE MOR	7590 09/24/200 RRIS LLP - Philadelphia	EXAMINER		
IP DEPARTM	ENT	NGUYEN, KHIEM D		
30 SOUTH 17 PHILADELPI	TH STREET IIA, PA 19103-4196		ART UNIT	PAPER NUMBER
			2823	
			MAIL DATE	DELIVERY MODE
			09/24/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)		
10/661,793	KAO ET AL.		
Examiner	Art Unit		
KHIEM D. NGUYEN	2823		

	KHIEM D. NGUYEN	2823					
The MAILING DATE of this communication appe	ars on the cover sheet with the o	correspondence add	ress				
THE REPLY FILED 29 August 2008 FAILS TO PLACE THIS AF	PLICATION IN CONDITION FOR	ALLOWANCE.					
 M The reply was filed after a final rejection, but prior to or on application, applicant must timely file one of the following i application in condition for allowance; (2) a Notice of Appe for Continued Examination (RCE) in compliance with 37 C periods: 	the same day as filing a Notice of a eplies: (1) an amendment, affidavi al (with appeal fee) in compliance	Appeal. To avoid abar t, or other evidence, w with 37 CFR 41.31; or	hich places the (3) a Request				
a) The period for reply expiresmonths from the mailing	date of the final rejection.						
b) The period for reply expires on: (1) the mailing date of this Ar no event, however, will the statutory period for reply expire la Examiner Note: If box 1 is checked, check either box (a) or (I	ter than SIX MONTHS from the mailing	date of the final rejection	n.				
MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f							
Extensions of time may be obtained under 37 CFR 1.136(a). The date on which the petition under 37 CFR 1.136(a) and the appropriate extension fee have been filled is the date for purposes of determining the period of extension and the corresponding amount of the fee. The appropriate extension fee under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the shortened statutory period for reply originally set in the final Office action; or (2) as set forth in (b) above, if checket. Any reply received by the Office later than three months after the malting date of the final rejection, even if timely filled, may reduce any searned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL							
 The Notice of Appeal was filed on A brief in compl filing the Notice of Appeal (37 CFR 41.37(a)), or any exter Notice of Appeal has been filed, any reply must be filed wi 	sion thereof (37 CFR 41.37(e)), to	avoid dismissal of the					
<u>AMENDMENTS</u>							
3. The proposed amendment(s) filed after a final rejection, but prior to the date of filing a brief, will not be entered because (a) hey raise new issues that would require further consideration and/or search (see NOTE below); (b) hy raise the issue of new matter (see NOTE below);							
 (c) ☐ They are not deemed to place the application in bett _ appeal; and/or 	er form for appeal by materially red	ducing or simplifying th	ne issues for				
(d) ☐ They present additional claims without canceling a c NOTE: (See 37 CFR 1.116 and 41.33(a)).	orresponding number of finally reje	ected claims.					
4. The amendments are not in compliance with 37 CFR 1.12	1. See attached Notice of Non-Cor	mpliant Amendment (F	PTOL-324).				
5. Applicant's reply has overcome the following rejection(s):							
 Newly proposed or amended claim(s) would be all non-allowable claim(s). 		•					
 For purposes of appeal, the proposed amendment(s): a) [how the new or amended claims would be rejected is prov The status of the claim(s) is (or will be) as follows: Claim(s) allowed: 12-14. 		I be entered and an ex	planation of				
Claim(s) objected to: <u>None</u> . Claim(s) rejected: <u>8-11 and 15-17</u> .							
Claim(s) withdrawn from consideration: None.							
AFFIDAVIT OR OTHER EVIDENCE							
 The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e). 							
 The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to or showing a good and sufficient reasons why it is necessary 	ercome <u>all</u> rejections under appea	al and/or appellant fails	s to provide a				
10. ☐ The affidavit or other evidence is entered. An explanation REQUEST FOR RECONSIDERATION/OTHER	of the status of the claims after er	ntry is below or attache	ed.				
 The request for reconsideration has been considered but <u>See Continuation Sheet.</u> 	does NOT place the application in	condition for allowan	ce because:				
12. Note the attached Information Disclosure Statement(s). (PTO/SB/08) Paper No(s) 13. Other:							
	/Khiem D. Nguyen/ Examiner, Art Unit 2823						

Continuation of 11. does NOT place the application in condition for allowance because: Applicants contend that the reference, Sahin et al. (U.S. Pub. 2003/0220708), herein known as Sahin provides no feedback communication to the means that creates the opining in the layer of etch resist material, much less feedback communication to the means that creates the opening in the layer of etch resist material for controlling the CD's of the opening, as in the claimed invention.

In response to Applicants' contention that Sahin does not teach or suggest said feedback mechanism communicating with said means for creating an opening through a layer of etch resist material to control said critical dimension measurement of said opening by implementing corrections in said means for creating an opening through a layer of etch resist material.

Applicants' attention is respectfully directed to (pages 16-17, paragraphs [0207]-[0212] and FIGS. A4(1) and A4(2)), where Sahin discloses a flow chart of a process for forming shallow trench isolation (STI) regions within a substrate including (step 806, FIG. A4(1)) or using a metrology tool 324b (see page 7, paragraphs [0100]-[0105] and FIG. 3) to measure the width, depth and/or profile of the openings formed within the patterned masking layer (patterned photoresist layer) (see page 16, paragraphs [0210]-[021])). The information obtained can be communicate to a module controller 114 (see page 5, paragraph [0049] and FIG. 1A, for example). If the obtained critical dimension (CD) measurement of the opening created through the patterned photoresist layer is not within design specification, then in (step 811, FIG. 8A(1)), the module controller 114 may reject the water as being out of design specification and may direct a inventive system 100 (see page 5, paragraphs [0070]-[0072] and FIG. 1B) to rework the water (step 807, FIG. 8A(1)) (see page 16, paragraph [0211)). If the controller 114 directs the etch tool 102 to perform an STI etch process based on the dimensions/profile of the openings of the patterned photoresist mask layer (see page 17, paragraph [0212]).

In view of the above, it is respectfully submitted that Sahin does provide a feedback mechanism that communicates with the means for creating an opening of the photonesis material layer and control the critical dimension measurement of the opining by implementing corrections in the means for creating an opening through the photoresist layer. Sahin discloses particularly in (page 16, paregraph [2020]) that, after the module controller 114 rejected the wafer for being not within the specification requirements. The wafer may be reprocessed via a lithography bool (not shown). Therefore, by doing so, Sahin providing a feedback mechanism for assuring that the obtained critical dimension measurement of the opening created through the photoresist layer is within design specification. The feedback mechanism communicates with the means for creating the opening created through the photoresist layer to implement necessary corrections to assure that the critical dimensions measurement of the opening is within design specification before conveying the wafer to the the etch tool 102 to perform an STI etch process (which creating an opening through the layer of insulation materials).

For this reason. Examiner holds the final rejection proper.